#### **Sensitive Gate Triacs**

#### **Silicon Bidirectional Thyristors**

Designed primarily for industrial and consumer applications for full—wave control of AC loads such as appliance controls, heater controls, motor controls, and other power switching applications.

#### **Features**

- Sensitive Gate Triggering in 3 Modes for AC Triggering on Sinking Current Sources
- Four Mode Triggering for Drive Circuits that Source Current
- All Diffused and Glass–Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance and High Heat Dissipation
- Center Gate Geometry for Uniform Current Spreading
- These Devices are Pb-Free and are RoHS Compliant\*



#### ON Semiconductor®

www.onsemi.com

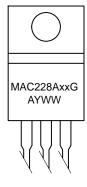
# TRIACS 8 AMPERES RMS 200 – 800 VOLTS





TO-220 CASE 221A STYLE 4

#### MARKING DIAGRAM



xx = 4, 6, 8, or 10

A = Assembly Location (Optional)\*

 $egin{array}{ll} Y &= Year \\ WW &= Work Week \\ G &= Pb-Free Package \\ \end{array}$ 

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

<sup>\*</sup> The Assembly Location code (A) is optional. In cases where the Assembly Location is stamped on the package the assembly code may be blank.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Peak Repetitive Off–State Voltage· (Note 1)  (T <sub>J</sub> = -40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open)  MAC228A  MAC228A  MAC228A1	16 18	200 400 600 800	V
On-State RMS Current, (T <sub>C</sub> = 80°C) – Full Cycle Sine Wave 50 to 60 Hz	I <sub>T(RMS)</sub>	8.0	Α
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>J</sub> = 110°C)	ITSM	80	А
Circuit Fusing Considerations, (t = 8.3 ms)	l <sup>2</sup> t	26	A <sup>2</sup> s
Peak Gate Current, (t ≤ 2 μs, T <sub>C</sub> = 80°C)	I <sub>GM</sub>	±2.0	Α
Peak Gate Voltage, (t ≤ 2 μs, T <sub>C</sub> = 80°C)	$V_{GM}$	±10	V
Peak Gate Power, (t ≤ 2 μs, T <sub>C</sub> = 80°C)	P <sub>GM</sub>	20	W
Average Gate Power, (t $\leq$ 8.3 ms, T <sub>C</sub> = 80°C)	P <sub>G(AV)</sub>	0.5	W
Operating Junction Temperature Range	TJ	-40 to 110	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to 150	°C
Mounting Torque	_	8.0	in lb

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such

#### THERMAL CHARACTERISTICS

Characteristic		Value	Unit
Thermal Resistance – Junction–to–Case		2.0	°C/W
Thermal Resistance – Junction–to–Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

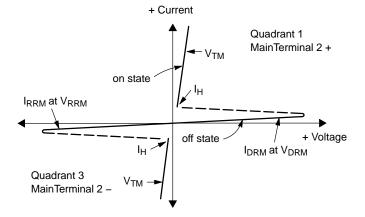
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Peak Repetitive Blocking Current, ( $V_D$ = Rated $V_{DRM}$ , $V_{RRM}$ ; Gate Open) $T_J$ = 25°C $T_J$ = 110°C	I <sub>DRM</sub> , I <sub>RRM</sub>	-	-	10 2.0	μA mA
ON CHARACTERISTICS	•	•	•		•
Peak On-State Voltage, (I <sub>TM</sub> = ±11 A Peak, Pulse Width ≤2 ms, Duty Cycle ≤2%)	$V_{TM}$	_	_	1.8	V
Gate Trigger Current (Continuous DC), (V <sub>D</sub> = 12 V, R <sub>L</sub> = 100 $\Omega$ ) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+)	l <sub>GT</sub>	- -	_ _	5.0 10	mA
Gate Trigger Voltage (Continuous DC), (V <sub>D</sub> = 12 V, R <sub>L</sub> = 100 $\Omega$ ) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+)	V <sub>GT</sub>	- -	_ _	2.0 2.5	V
Gate Non–Trigger Voltage (Continuous DC), (V <sub>D</sub> = 12 V, T <sub>C</sub> = 110 $^{\circ}$ C, R <sub>L</sub> = 100 $\Omega$ ) All Four Quadrants	V <sub>GD</sub>	0.2	-	-	V
Holding Current, (V <sub>D</sub> = 12 Vdc, Initiating Current = ±200 mA, Gate Open)	lΗ	_	-	15	mA
Gate–Controlled Turn–On Time, (V <sub>D</sub> = Rated V <sub>DRM</sub> , I <sub>TM</sub> = 16 A Peak, I <sub>G</sub> = 30 mA)	t <sub>gt</sub>	_	1.5	_	μS
DYNAMIC CHARACTERISTICS					
Critical Rate of Rise of Off-State Voltage, ( $V_D$ = Rated $V_{DRM}$ , Exponential Waveform, $T_C$ = 110°C)	dv/dt	-	25	-	V/μs
Critical Rate of Rise of Commutation Voltage, ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 11.3 A, Commutating di/dt = 4.1 A/ms, Gate Unenergized, $T_C$ = 80°C)	dv/dt(c)	_	5.0	_	V/μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

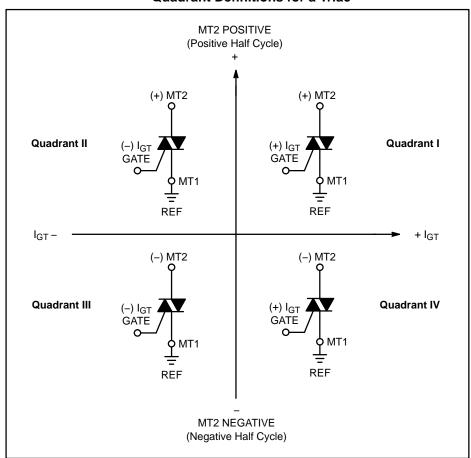
that the voltage ratings of the devices are exceeded.

## Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current

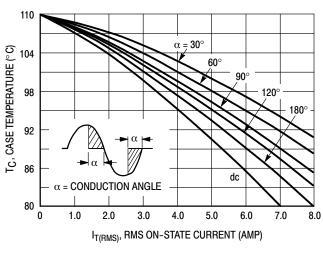


#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

 $\dot{\text{With}}$  in–phase signals (using standard AC lines) quadrants I and III are used.



10 P(AV) AVERAGE POWER (WATTS) 8.0  $\alpha$  = CONDUCTION ANGLE 120° 6.0 90°  $T_J \approx 110^{\circ} C$ 4.0 2.0 0 1.0 2.0 3.0 4.0 5.0 6.0 7.0 8.0  $I_{T(RMS)}$ , RMS ON-STATE CURRENT (AMP)

Figure 1. RMS Current Derating

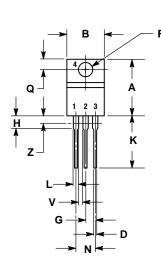
Figure 2. On-State Power Dissipation

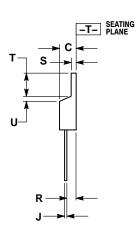
#### ORDERING INFORMATION

Device	Package	Shipping	
MAC228A4G	TO-220 (Pb-Free)	500 Units / Bulk	
MAC228A6G	TO-220 (Pb-Free)	500 Units / Bulk	
MAC228A6TG	TO-220 (Pb-Free)	50 Units / Rail	
MAC228A8G	TO-220 (Pb-Free)	500 Units / Bulk	
MAC228A8TG	TO-220 (Pb-Free)	50 Units / Rail	
MAC228A10G	TO-220 (Pb-Free)	500 Units / Bulk	

#### PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH** 





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE

MULIMETERS

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 4:

PIN 1. MAIN TERMINAL 1

- MAIN TERMINAL 2 2.
- 3. GATE
- MAIN TERMINAL 2

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